mmTron
Unleashing the mmWave Frontier

TMC200-D
DC-28 GHz Distributed Power Amplifier

Product Features

- RF frequency: DC to 28 GHz
- Linear Gain: 15 dB
- P_{sat}: 2.5 W
- Die Size: X=3 mm, Y=1.9 mm, Z=0.1mm
- Package Size: X=5 mm, Y=5 mm, Z=2mm
- DC Power: 15 VDC, 550 mA

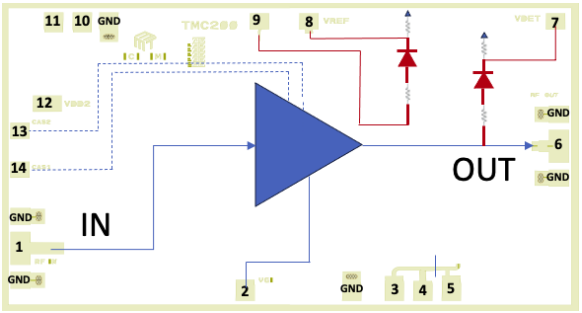
Applications

- Point-to-Point Radios and VSATs
- Test instrumentation
- Fiber Optics
- Military, EW and Space

Product Description

The TMC200-D GaAs PHEMT Distributed amplifier is a broadband device, designed for use in Radios, Test instrumentation, Military, EW and Space applications. The TMC200-D is a 50 W matched design with positive gain slope providing 2.5W of saturated power to 28 GHz, excellent power added efficiency and eliminates the need for RF port matching. TMC200-D is exceptionally linear with minimal variation over temperature. The typical bias for TMC200-D is 10-15V and 450-550mA but it can be biased to as low as 8V and 300mA with excellent performance. Both bond pad and backside metallization are Au-based that is compatible with ribbon and wedge bonding and high conductivity epoxy and eutectic die attach methods. TMC200-P5 is the 5x5 packaged version.

Functional Block Diagram



Ordering Information

Part No.	Description
TMC200-D	Bare Die
TMC200-P5	5x5 Package

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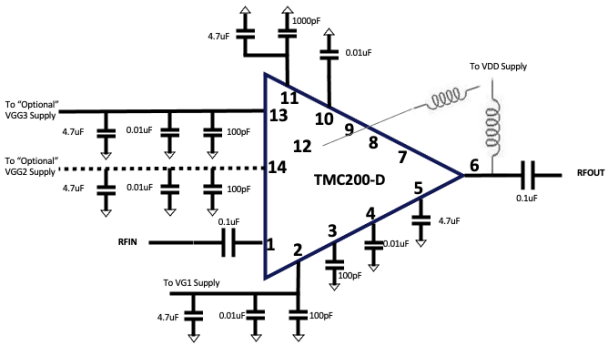
Typical Operating Conditions

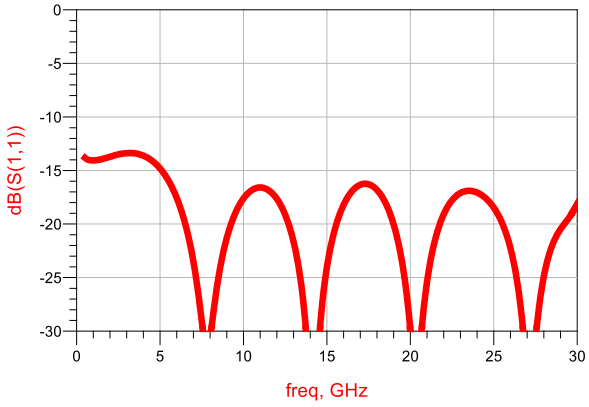
	Min	Typ	Max	
Frequency	DC		28	GHz
Gain		15		dB
P1dB		33		dBm
Psat		34		dBm
Noise Figure		3.5		dB
OIP3		43		dBm
Bias Voltage		15		V
Bias Current		550		mA

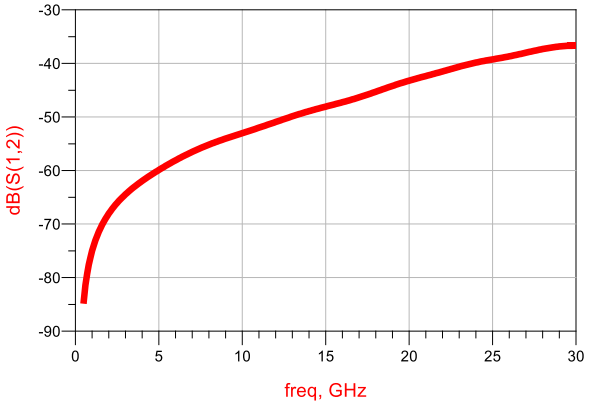
* Electrical Performance : Vdd = 15 V, VGG = -0.5 V, TA = 25 °C, F=20 GHz

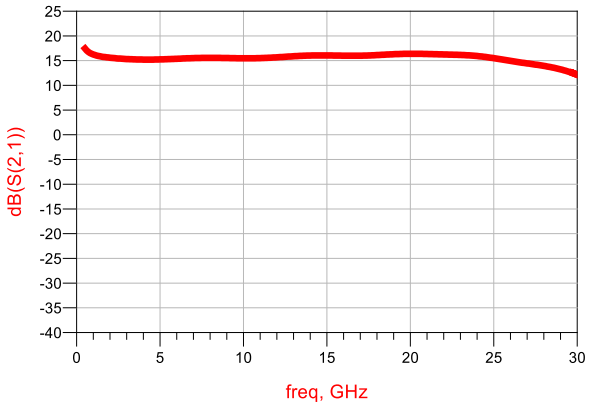
Application Circuit TMC200

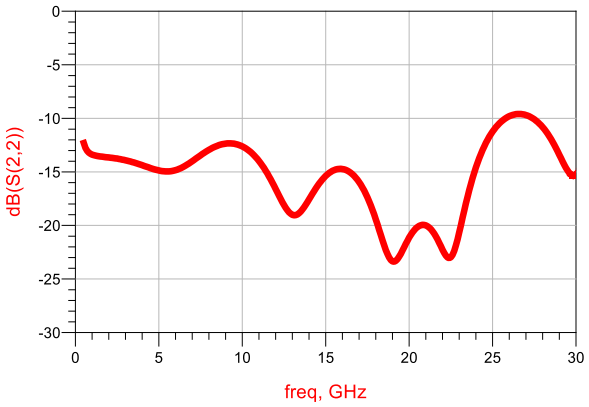


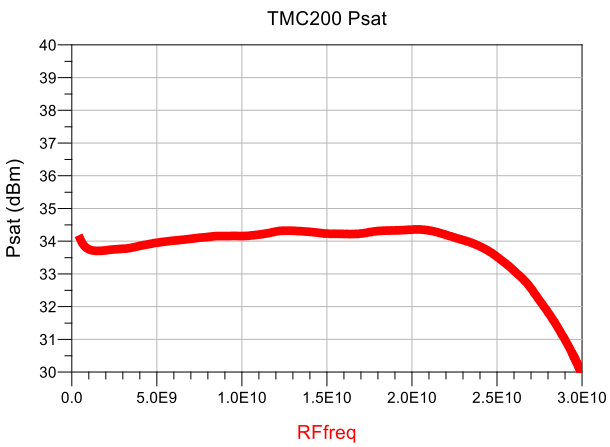
TMC200, 15V/550mA Performance Charts





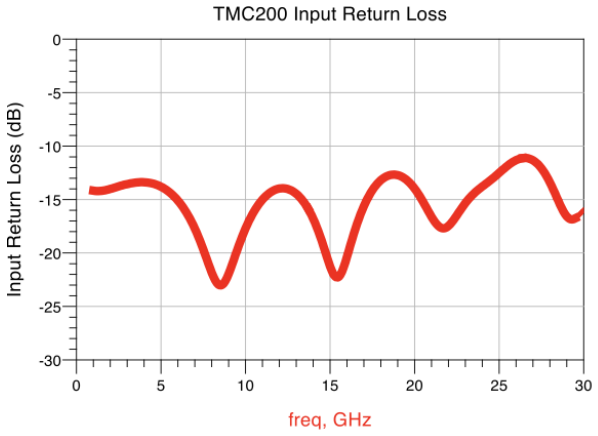


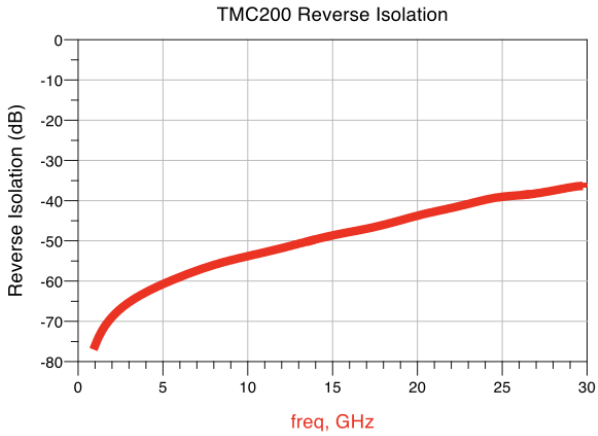


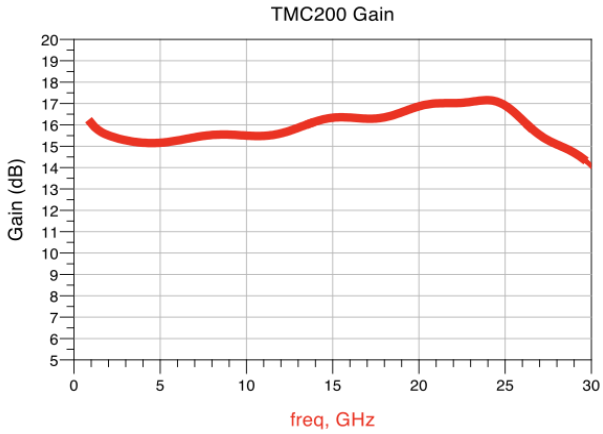


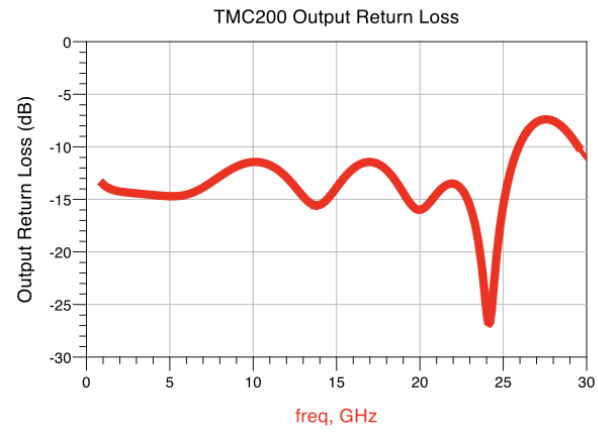


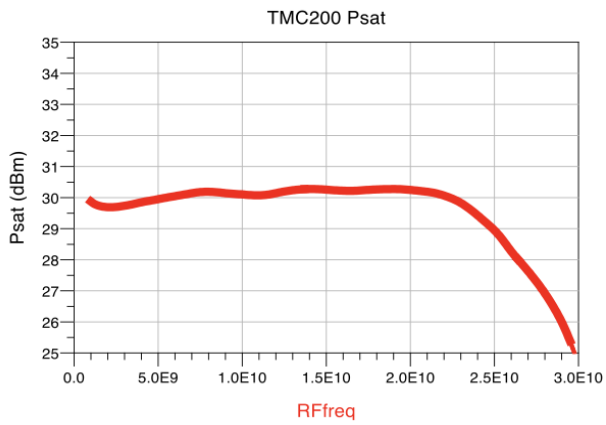
TMC200, 10V/500mA Performance

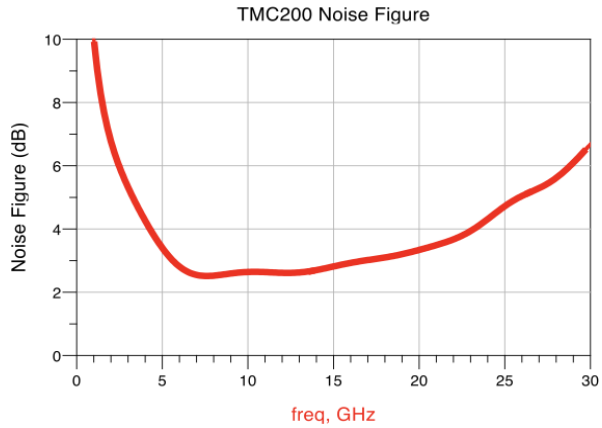


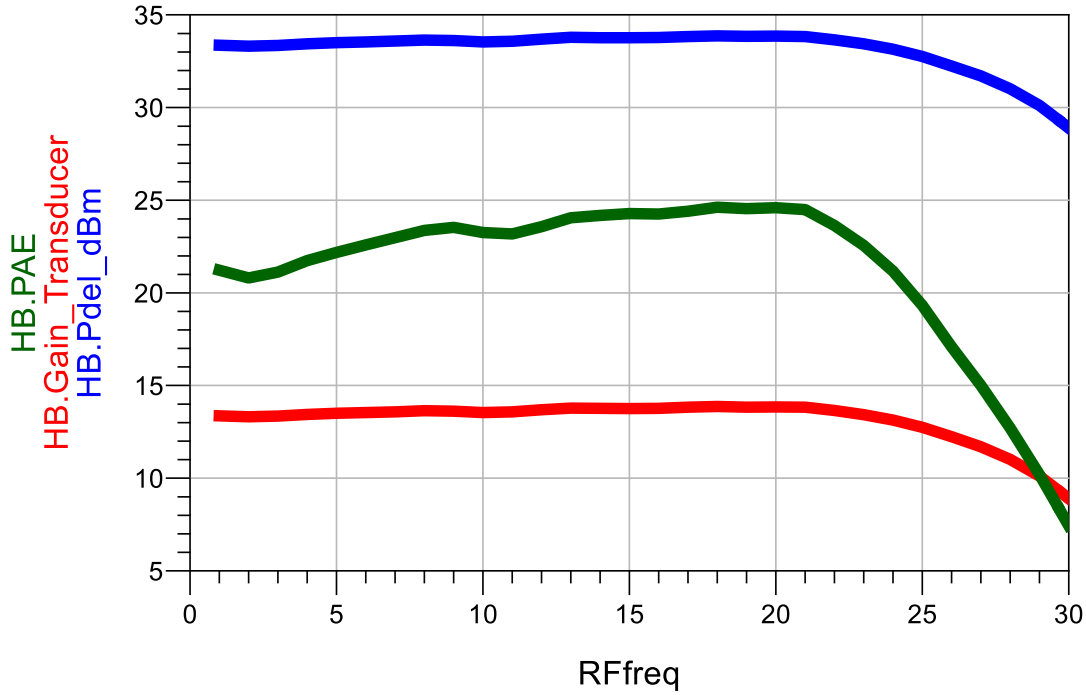








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HB.Gain_Transducer
HB.Pdel_dBm
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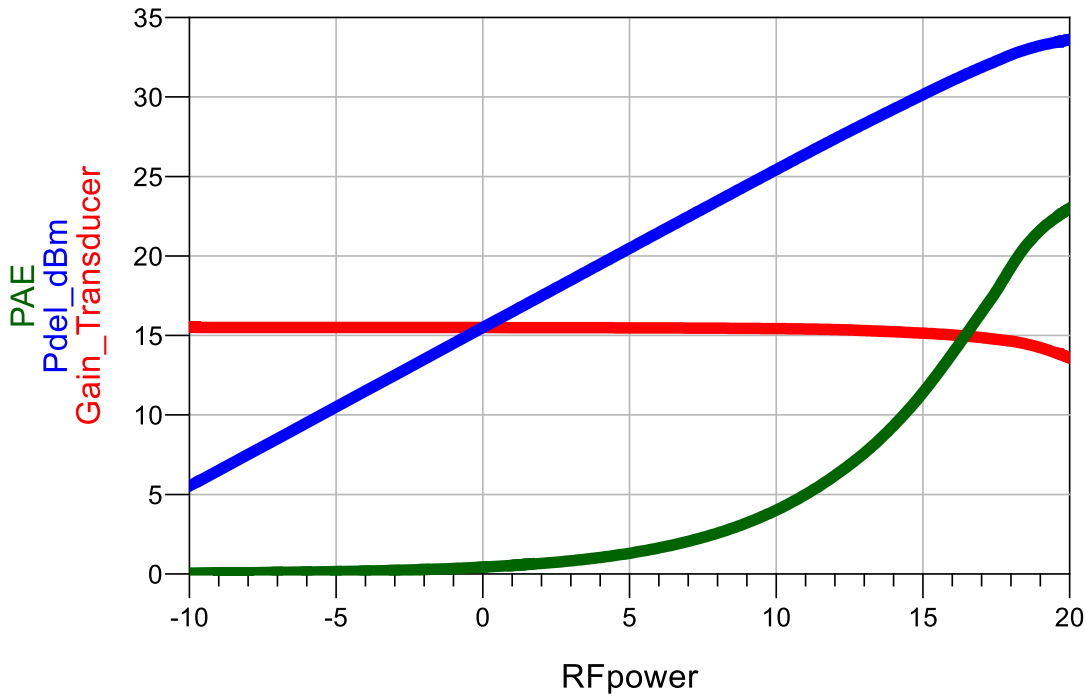
RFfreq


PAE
Pdel_dBm
Gain_Transducer
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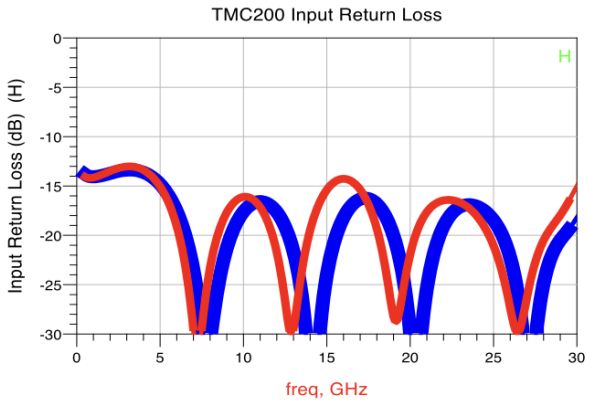
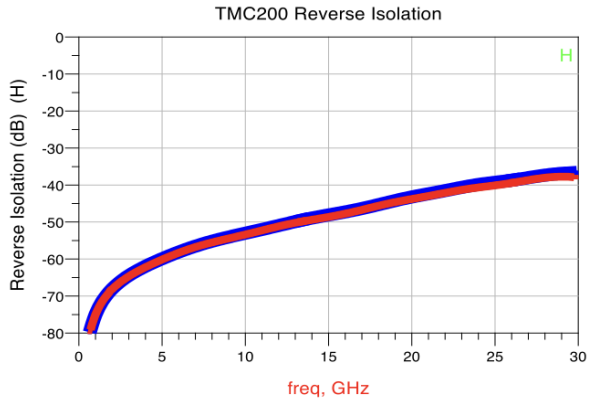
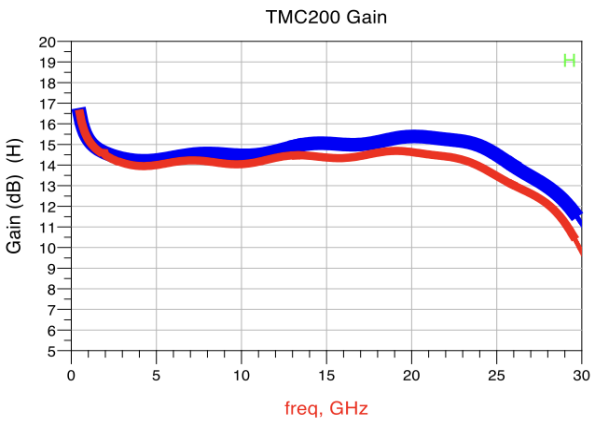
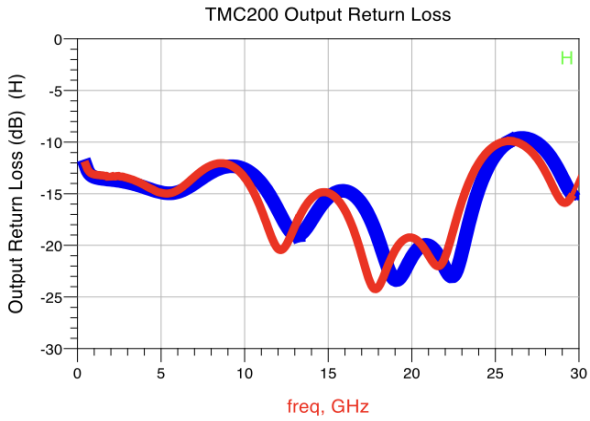
RFpower

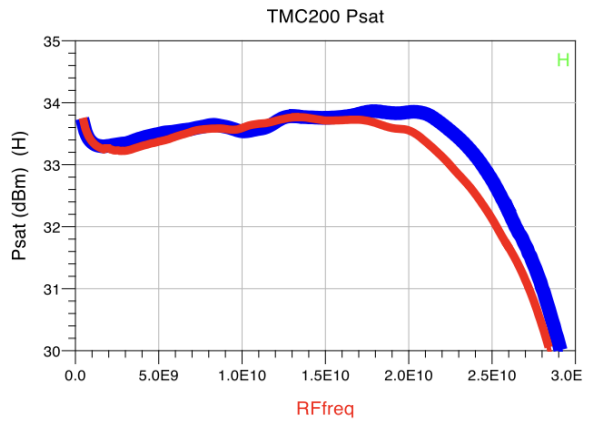
TMC200, Bare Die vs. Packaged Device Performance

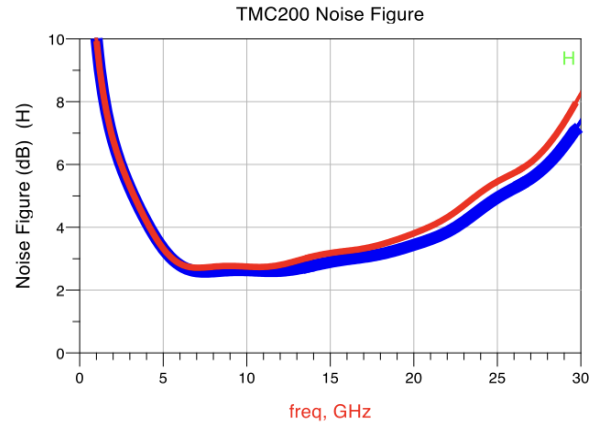






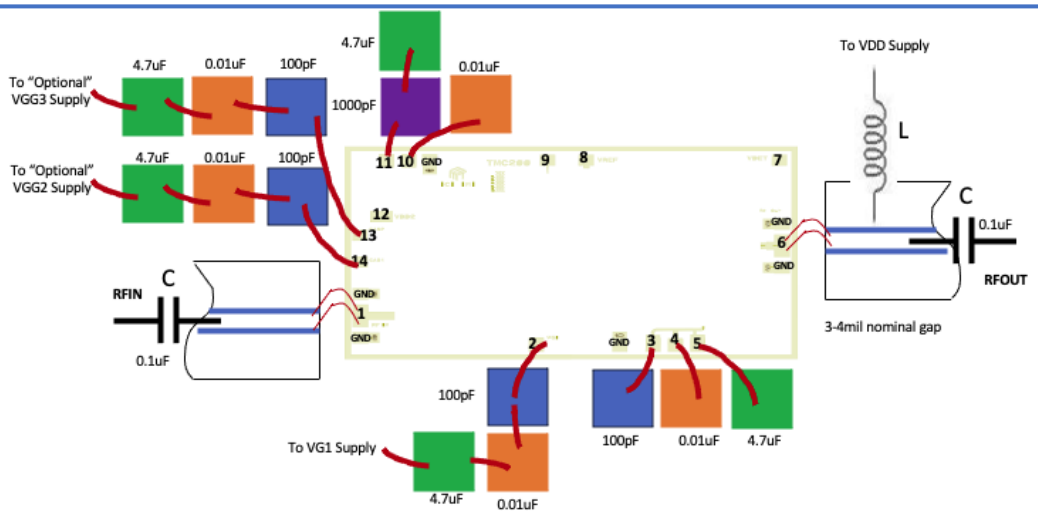


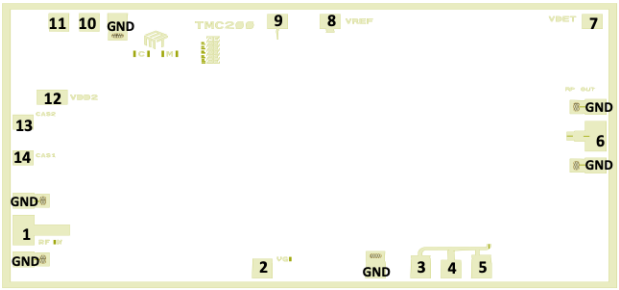




Blue: Bare Die TMC200-D
Red: Packaged TMC200-P5

Assembly Drawing, Layout and Pin/Pad Description





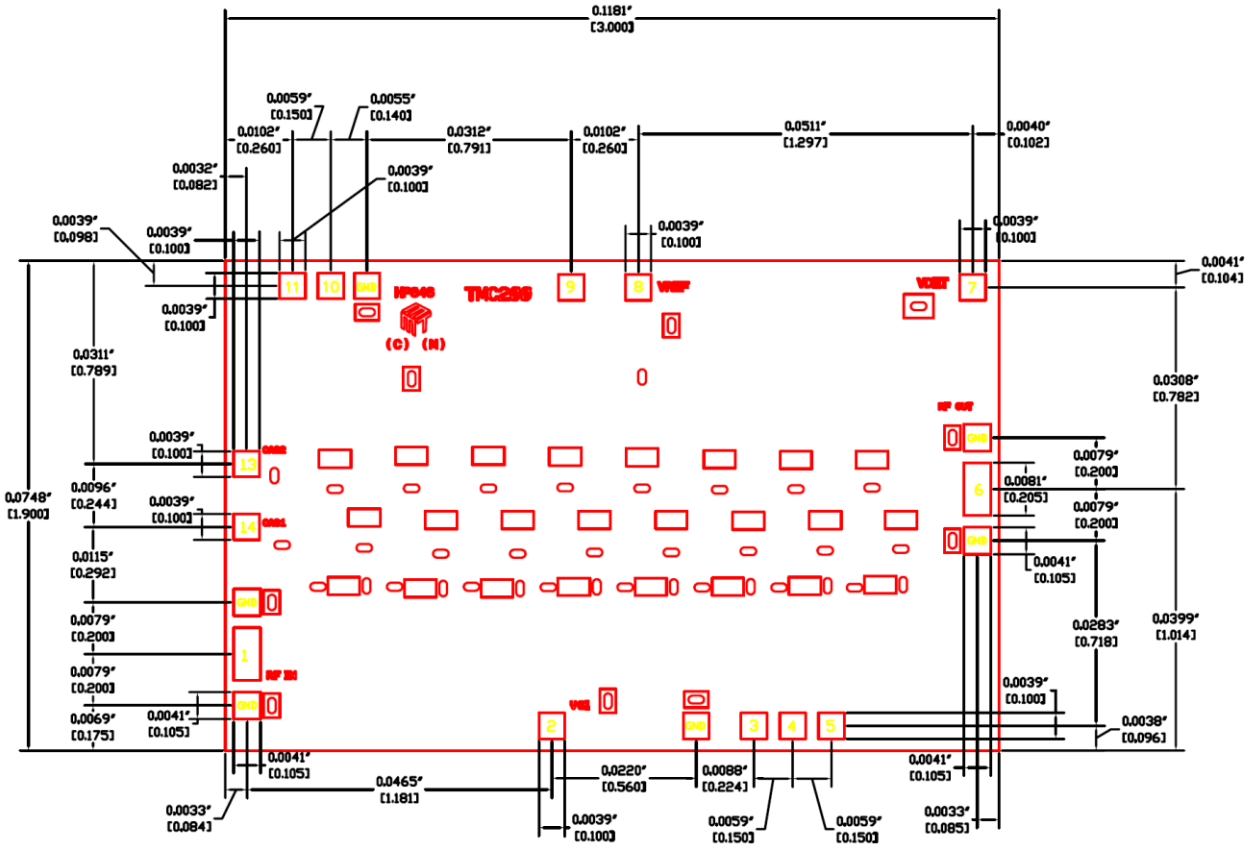
Recommended Biasing

The TMC200-D is operated with one positive supply VDD and one negative supply voltage VGG. The positive supply must be connected to the output pad through a bias-T. The negative voltage VGG should be connected to VG1 pad on the die. The VGG is biased to -1V first, then VDD is gradually biased to +10V and finally, VG1 is adjusted to around -0.5V for IDD=500mA DC current.

Reverse the sequence during power down, i.e. bring the VGG to -1V, lower VDD to 0V, and then VGG to 0.

Pad #	Function	Description
1	RF INPUT	This pad is DC coupled and matched to 50 Ohms. Blocking capacitor is required.
2	VGG1 BIAS	Gate control 1 for amplifier. Attach 100pF/0.01uF/4.7 uF chip bypass capacitors.
3	ACG4	Low frequency termination. Attach 100pF chip bypass capacitor.
4	ACG3	Low frequency termination. Attach 0.01 uF chip bypass capacitor.
5	ACG5	Low frequency termination. Attach 4.7 uF chip bypass capacitor.
6	RF OUTPUT & VDD	RF output for amplifier. Connect DC bias (Vdd) network to provide drain current (Idd).
7	VDET	Temperature compensate power detector output voltage. This provides a voltage proportional to the output power of the amplifier.

Pad#	Function	Description
8	VREF	Detector DC Offset Voltage
9	VREF_VDC	Detector VDC. Used in conjunction with VREF for common mode cancellation of diode temperature drift and good log linearity vs. power.
10	ACG2	Low frequency termination. Attach 0.01 uF chip bypass capacitor.
11	ACG1	Low frequency termination. Attach 1000pF/4.7uF chip bypass capacitor.
12	VDD2	Optional: Second connection for DC bias (Vdd) network to provide a 2nd path for drain current (Idd) for higher power applications. See application circuit herein.
13	VGG2 (VCAS2)	Gate 3 for amplifier. Attach 100pF/0.01uF/4.7uF chip bypass capacitors. Typical operation has VGG3(VCAS2) biased internal to IC. Setting VGG3 externally can be used to adjust NF, Gain and OIP3.
14	VGG2 (VCAS1)	Gate 2 for amplifier. Optional: Attach 100pF/0.01uF/4.7uF chip bypass capacitors. Typical operation has VGG2(VCAS1) biased internal to IC. Setting VGG2 externally can be used to adjust NF, Gain and OIP3.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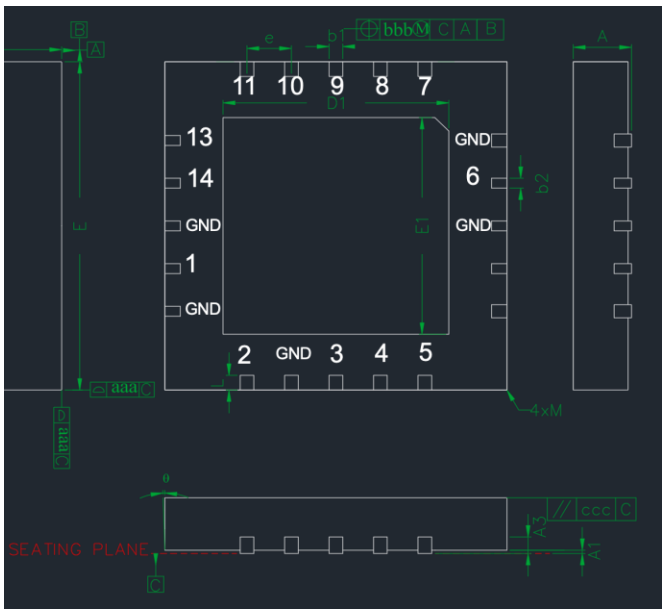
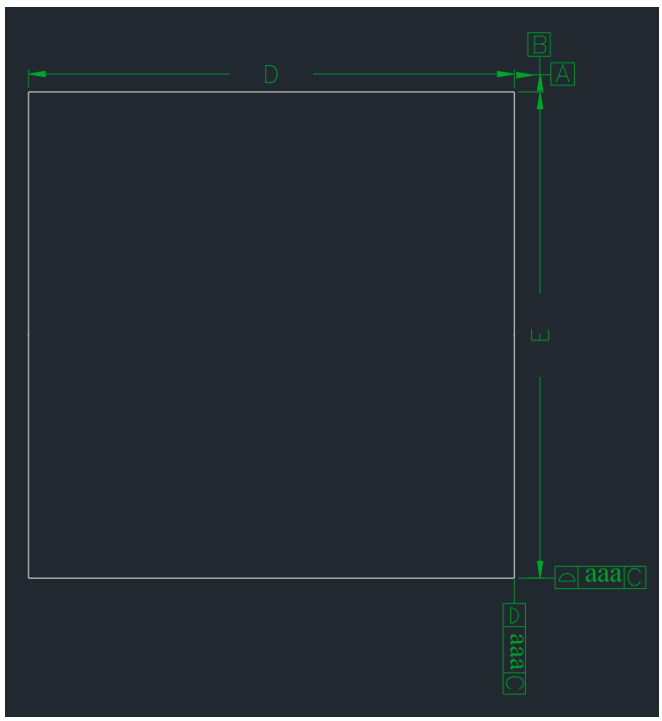
Layout Drawings

Pad #	Function
1	RF INPUT
2	VGG1 Bias
3	ACG4
4	ACG3
5	ACG5
6	RF OUTPUT & VDD
7	VDET
8	VREF
9	VREF_VDC
10	ACG2
11	ACG1
13	VGG2 (VCAS2)
14	VGG2 (VCAS1)



SYMBOLS	DIMENSIONS IN MILLIMETERS		
	MIN	NOM	MAX
A	0.80	0.90	1.00
A1	0	0.02	0.05
A3	——	0.25REF.	——
b1	0.15	0.20	0.25
b2	0.10	0.15	0.20
D	4.90	5.00	5.10
D1	——	3.30BSC	——
E	4.90	5.00	5.10
E1	——	3.30BSC	——
e	——	0.65BSC	——
L	0.18	0.23	0.28
θ	0	——	12°
aaa	——	0.25	——
bbb	——	0.10	——
ccc	——	0.10	——
M	——	——	0.05



Assembly Techniques

The TMC200-D is fabricated using a GaAs-based semiconductor material structure. All bare die are placed in Gel based ESD protective containers, and then sealed in an ESD protective bag for shipment. Once the sealed ESD protective bag has been opened, all die should be stored in a humidity-controlled dry nitrogen environment.

Use a vacuum collet sized to handle the chip along the edges to avoid touching the air bridges. The die is back-metalized and can be mounted with standard AuSn eutectic or conductive epoxy assembly techniques. The mounting surface should be clean and flat.

Eutectic Die Attach:

The most common eutectic alloy used in die attach is the gold-tin (AuSn) alloy. With a melting point of 280°C, it provides a strong, reliable bond without requiring excessively high temperatures that could potentially damage the die or the substrate. Eutectic die attach is generally performed in a two-step process. First, the eutectic alloy is deposited onto the die or substrate, often by a process such as electroplating or sputtering. This forms what is known as the "preform". Next, the die is placed onto the preform, and the assembly is heated to the melting point of the alloy. This causes the alloy to reflow, spreading out to cover the entire interface between the die and the substrate. Once cooled, the alloy solidifies, creating a robust bond between the die and the substrate. A 80/20 AuSn preform with a work surface temperature of 255 °C is recommended. The tool temperature of 265 °C should be used. The chip should not be exposed to a temperature greater than 300 °C for more than 45 seconds. A maximum 3 seconds of scrubbing should be sufficient for die attachment.

Epoxy Die Attach:

Apply a minimum amount of epoxy such as Ablestick 84-1LMI m(0.25-0.75mil) to the mounting surface so that a thin epoxy fillet is observed around the perimeter of the chip once it is placed into position. Cure epoxy per the manufacturer's schedule. The epoxy fillet around the die should be approximately half-way up the side of the 4-mil thick MMIC. Too little epoxy may lead to voids, too much epoxy may lead to stringers and shorts to the front-side metal.

Wire Bonding:

RF wedge bonds made with two 1 mil wires are recommended for RF ports. A single 1mil wire can be used for DC pads. Ensure the bonding tool is grounded. These bonds could be bonded thermosonically with a force of 50 grams and a stage temperature of 150 °C. Use a shim under the die to bring the top surface of the die level with the RF input and output transmission line to shorten wirebonds to < 10mil.

Absolute Maximum Ratings

Parameter	Value / Range
Drain Bias Voltage (VDD)	+16 V
Gate Bias Voltage (VG1)	-2 to 0 V
Gate Bias Current (IG1)	+10 mA
RF Input Power (RFIN) (VDD=+12V)	+24 dBm
Channel Temperature	175 °C
Continuous Pdiss, (T=85°C) (derate 109 mW/°C above 85 °C)	9.2 W
Thermal Resistance (channel to die bottom)	9.8 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature for MTTF>1E6 hrs.	-55 to +125 °C

NOTE: Operation of TMC200 outside the parameter ranges given above can cause irreversible damage.



Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. mmTron Inc. recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications. III-V MMICs are ESD-sensitive. Preventative ESD measures must be employed in all aspects of storage, handling, and assembly. MMIC ESD precautions, handling considerations, and die-attach and bonding methods are critical factors in successful III-V MMIC performance and reliability.



RoHS Compliant

This part is RoHS compliant, meeting the requirements of the EU Restriction of Hazardous Substances Directive 2002/95/EC, commonly known as RoHS. Six substances are regulated: lead, mercury, cadmium, chromium VI (hexavalent chromium), polybrominated biphenyls (PBB), and polybrominated biphenyl ethers (PBDE). RoHS compliance requires that any residual concentration of these substances is below the Directive's maximum concentration values (MCV): cadmium 100ppm by weight and all others 1000ppm by weight.

Disclaimer and Warranty Statement

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